

MJB41C, NJVMJB41CT4G (NPN), MJB42C, NJVMJB42CT4G (PNP)

Complementary Silicon Plastic Power Transistors

D²PAK for Surface Mount

Features

- Lead Formed for Surface Mount Applications in Plastic Sleeves (No Suffix)
- Electrically the Same as TIP41 and T1P42 Series
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb-Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	100	Vdc
Collector-Base Voltage	V_{CB}	100	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous – Peak	I_C	6.0 10	Adc
Base Current	I_B	2.0	Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	65 0.52	W W/ $^\circ\text{C}$
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	2.0 0.016	W W/ $^\circ\text{C}$
Unclamped Inductive Load Energy (Note 1)	E	62.5	mJ
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.92	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from Case for 10 Seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $I_C = 2.5\text{ A}$, $L = 20\text{ mH}$, P.R.F. = 10 Hz, $V_{CC} = 10\text{ V}$, $R_{BE} = 100\ \Omega$

2. When surface mounted to an FR-4 board using the minimum recommended pad size.



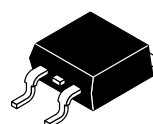
ON Semiconductor®

<http://onsemi.com>

COMPLEMENTARY SILICON POWER TRANSISTORS

6 AMPERES, 100 VOLTS, 65 WATTS

MARKING DIAGRAM



D²PAK
CASE 418B
STYLE 1



J4xC = Specific Device Code
x = 1 or 2
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MJB41CG	D ² PAK (Pb-Free)	50 Units / Rail
MJB41CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NJVMJB41CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
MJB42CG	D ² PAK (Pb-Free)	50 Units / Rail
MJB42CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel
NJVMJB42CT4G	D ² PAK (Pb-Free)	800 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (Note 3) ($I_C = 30\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	100	–	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CEO}	–	0.7	mAdc
Collector Cutoff Current ($V_{CE} = 100\text{ Vdc}$, $V_{EB} = 0$)	I_{CES}	–	100	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	50	μAdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = 0.3\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$) ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	h_{FE}	30 15	– 75	–
Collector-Emitter Saturation Voltage ($I_C = 6.0\text{ Adc}$, $I_B = 600\text{ mAdc}$)	$V_{CE(sat)}$	–	1.5	Vdc
Base-Emitter On Voltage ($I_C = 6.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$)	$V_{BE(on)}$	–	2.0	Vdc

DYNAMIC CHARACTERISTICS

Current-Gain – Bandwidth Product ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f_{\text{test}} = 1.0\text{ MHz}$)	f_T	3.0	–	MHz
Small-Signal Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	20	–	–

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

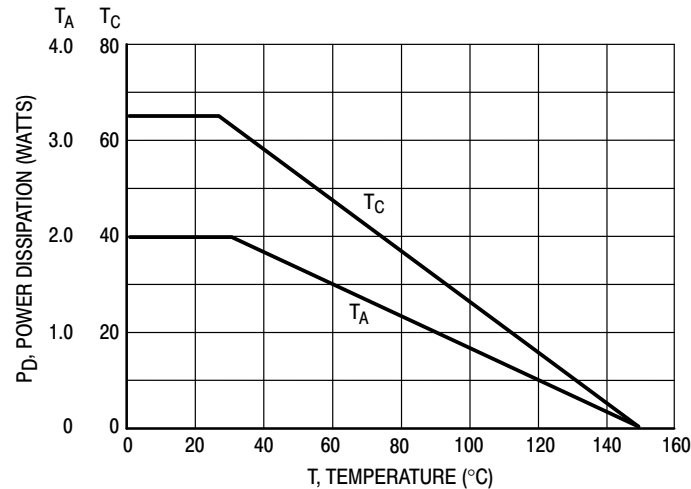


Figure 1. Power Derating

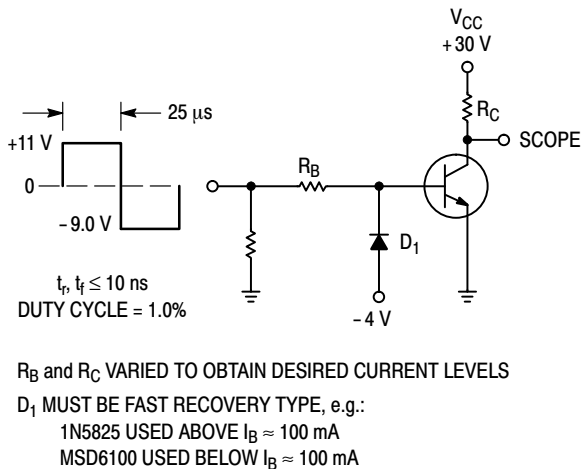


Figure 2. Switching Time Test Circuit

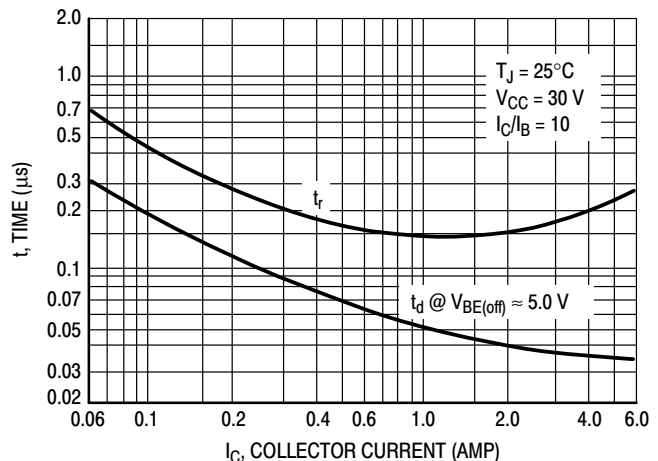


Figure 3. Turn-On Time

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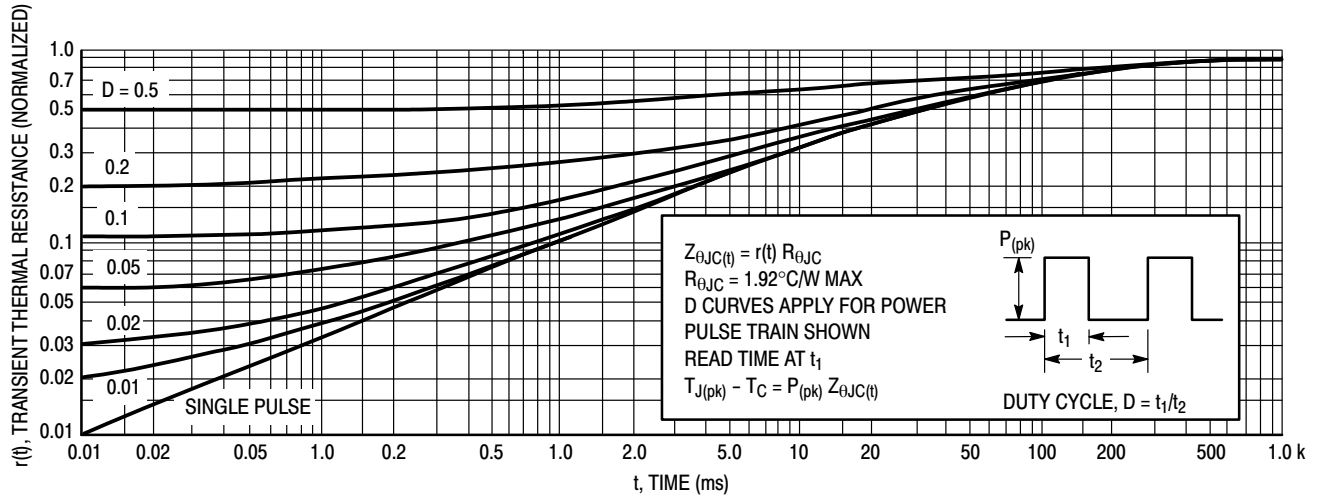


Figure 4. Thermal Response

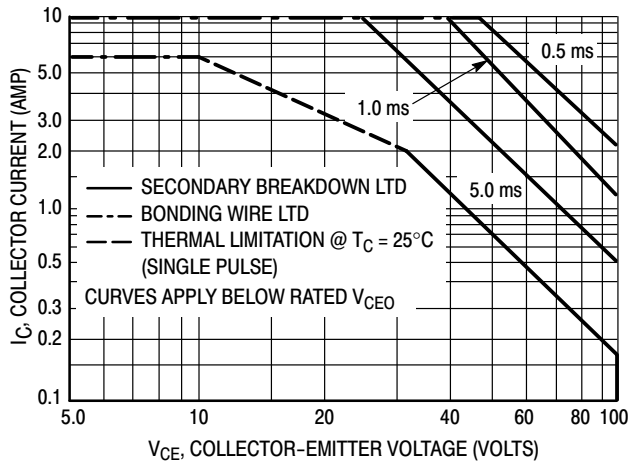


Figure 5. Active-Region Safe Operating Area

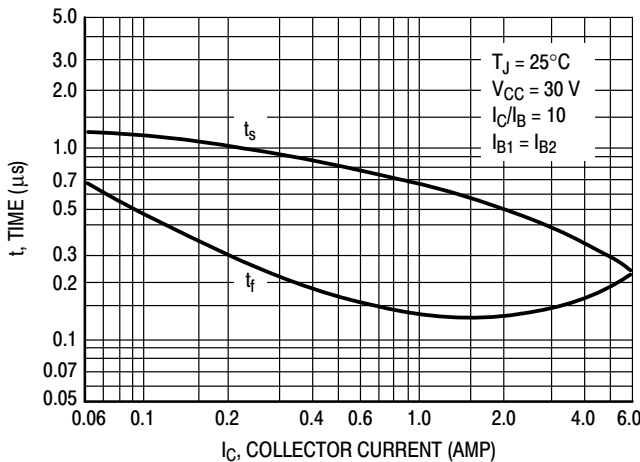


Figure 6. Turn-Off Time

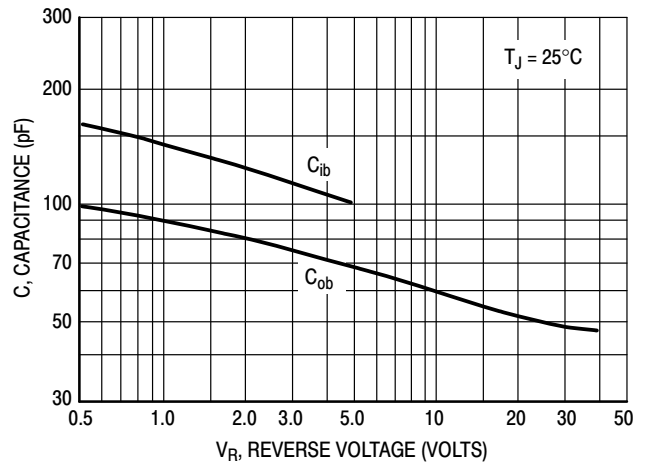


Figure 7. Capacitance

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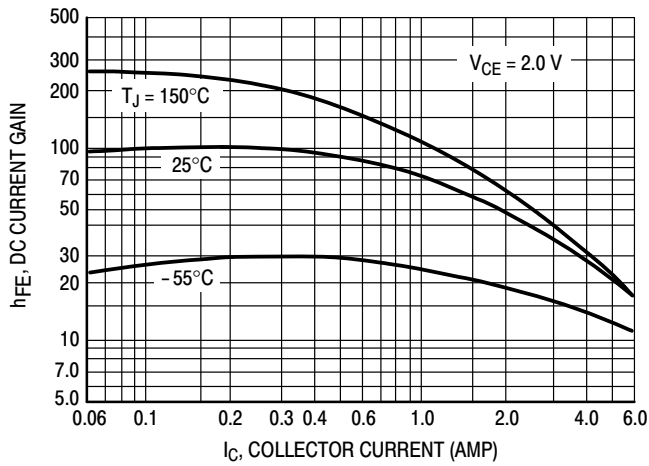


Figure 8. DC Current Gain

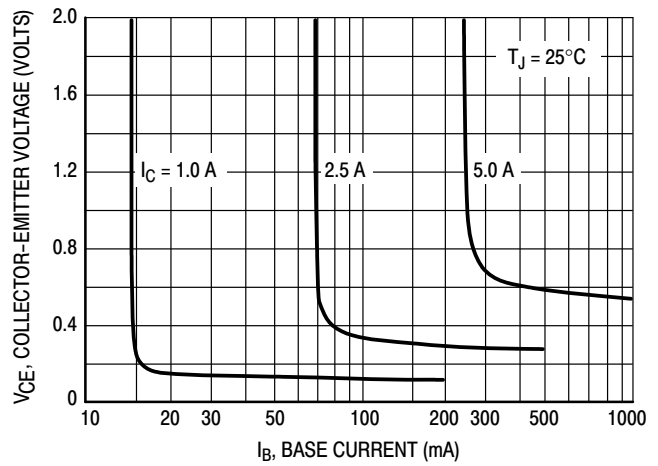


Figure 9. Collector Saturation Region

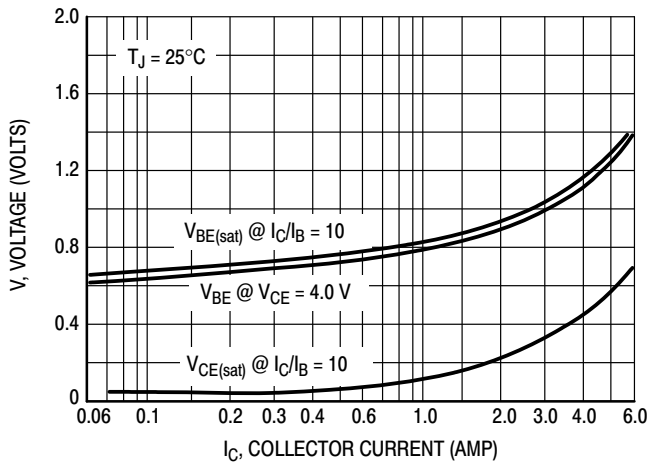


Figure 10. "On" Voltages

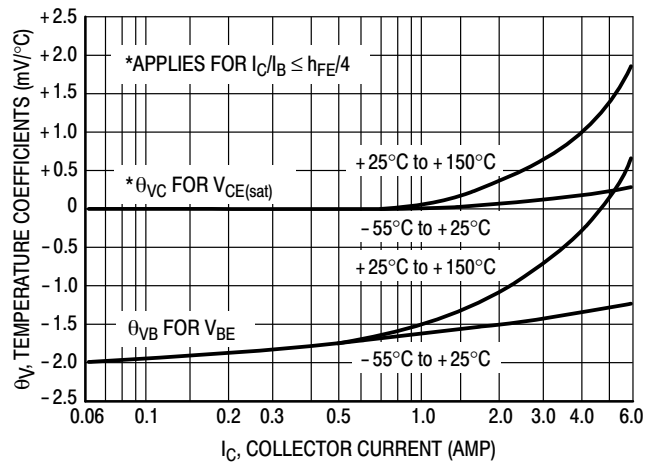


Figure 11. Temperature Coefficients

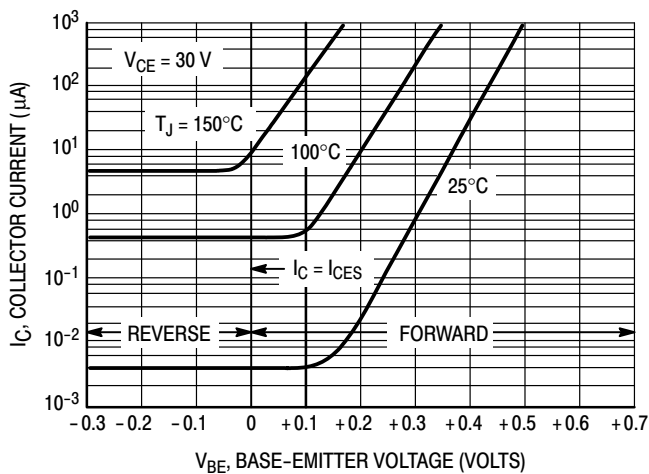


Figure 12. Collector Cut-Off Region

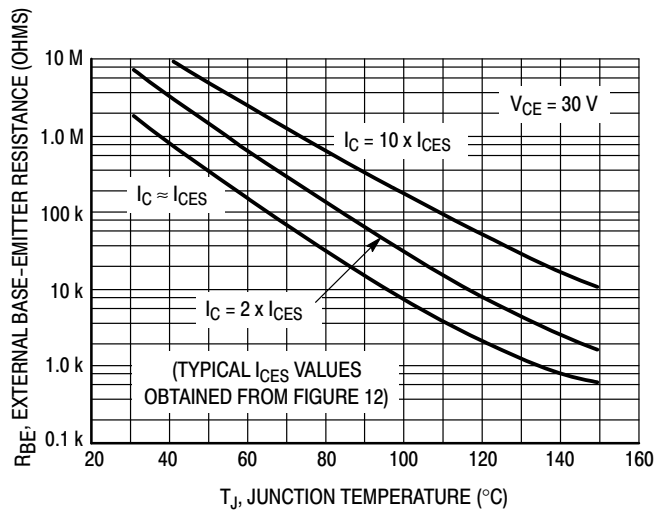
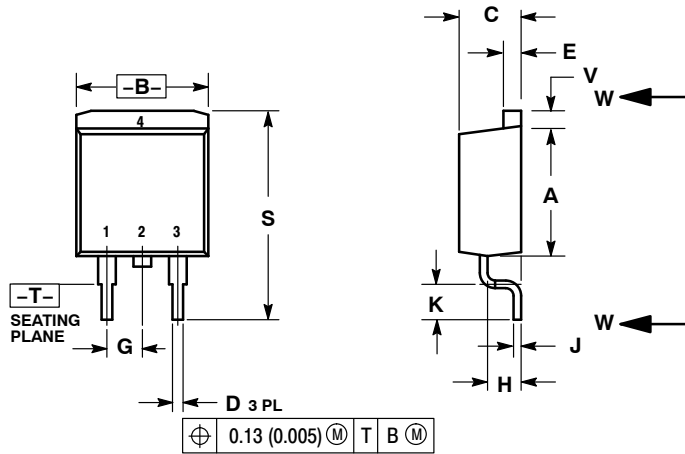


Figure 13. Effects of Base-Emitter Resistance

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PACKAGE DIMENSIONS

D²PAK 3 CASE 418B-04 ISSUE K



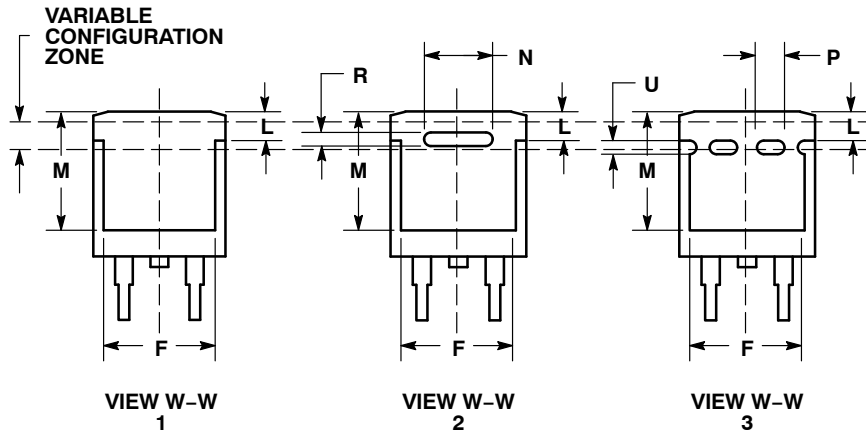
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

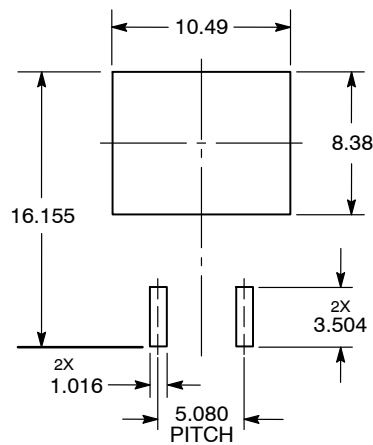
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 1:

- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR



SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.